Organisational Information

For registration please use the registration form which is available on the ECPE web page; www.ecpe.org > ECPE Events > ECPE Workshops: ECPE Workshop: Drivers, Control and Protection Circuits for MOSFETs and IGBTs> Registration Form

www.ecpe.org/ecpe-events

Deadline for registration:

> 12 October 2015

Participation fee:

- € 595,- * for industry \geq
- \geq € 445,- * for universities/institutes
- \triangleright € 150,- * for students/PhD students (copy of student ID requested)
 - (limited number only) (optional dinner: € 50,-* extra fee)

*plus 19 % German VAT

- The participation fee includes dinner, lunch, \geq coffee/soft drinks and a CD with the workshop presentations. Students/PhD students can book the dinner for an extra fee of \in 50,-*.
- A printed version of the workshop handout is \geq available on request (\in 50,-*).
- \triangleright With the confirmation of registration by email you are registered for the workshop and the invoice will be sent by post.
- Three participants from each ECPE member \geq company free of charge. Allocation in sequence of registration.
- \geq Further information (hotel list and maps) will be provided after registration and is available on the ECPE web page.
- In case of cancellation later than two weeks \geq before beginning or non-attendance 50 % of the participation fee is payable.

Organisational Information

Organiser	ECPE e.V. 90443 Nuremberg, Germany www.ecpe.org
Chairmen	Prof. Dr. Axel Mertens, Leibniz Universität Hannover Dr. Samuel Araujo, University of Kassel / KDEE Jochen Koszescha, ECPE e.V.
Organisation	Ingrid Bollens, ECPE e.V. +49 (0)911 / 81 02 88 – 10 Ingrid.bollens@ecpe.org
Venue	Sheraton Hannover Pelikan Hotel Pelikanplatz 31 30177 Hannover Germany

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ECPE Workshop

Drivers, Control and Protection Circuits for MOSFETs and IGBTs





Hannover

Germany

ECPE Workshop

Drivers, Control and Protection Circuits for MOSFETs and IGBTs

21 – 22 October 2015 Hannover, Germany

Progress in microelectronics and in the implementation of cheap sensors allows to increase the functionality of gate drive units for MOSFETs and for IGBTs. Functions like gate current control, closer observation of voltages and of current slopes can be implemented on gate drivers at low incremental cost. Advanced solutions for the isolation barrier with enhanced bi-directional communication lead to completely new possibilities. They can be used for better switching performance, better protection or for condition monitoring of the power semiconductors and modules.

In the context of the development and adoption of innovative Wide-Band-Gap semiconductors, new challenges concerning robust operation at very fast switching speed and frequencies also need to be addressed in order to attain the expected gains at system level. Nevertheless, without the necessary level of robust operation under all foreseen operating conditions, new and future solutions will be not accepted by developers and users. With this workshop we want to highlight again the state-of-the-art of advanced gate drive technology, and we will discuss what we can expect in the near future.

The workshop is chaired by

Prof. Dr. Axel Mertens (Leibniz Universität Hannover) Dr. Samuel Araujo (University of Kassel) Jochen Koszescha (ECPE e.V.)

All presentations and discussions will be in English language.

Programme

Wednesday, 21 October 2015

9:00 Start of Registration / Welcome Coffee

9:30 Welcome, Opening A. Mertens, Univ. Hannover / S. Araujo, Univ. Kassel J. Koszescha, ECPE e.V.

Introduction

9:45 Enhanced Functionality of Gate Units by Progress of Analog and Digital Electronics A. Mertens, Leibniz Universität Hannover

Session - Advanced Gate Control (& Protection)

- 10:30 IGBT Gate Drive with Current Control C. Hornstein, Conti Temic microelectronic
- 11:00 Digital Communication via Pulse Transformers M. Kettler, Semikron Elektronik
- 11:30 Protection Concept for PV Inverter Power Stages U. Stickelmann, SMA Solar Technology

12:00 Discussion

Lunch

Session - Monitoring

12:20

- **Reliable Short Circuit Turn-off** 13:20 M. Hornkamp, Power Integrations 13:50 High Power, Fast Switching Gate Driver with Isolated NTC Interface C. Balke, Maccon 14:20 Gate Driver with integrated IGBT Temperature sensing L. Beaurenaut, Infineon Technologies 14:50 Discussion 15:10 Coffee break **Session - Temperature Measurement** Estimation of the IGBT Junction Temperature 15:40 with Temperature Sensitive Parameters S. Weber, Leibniz Universität Hannover In-service Model-based Health Monitoring of 16:10 **IGBT Power Modules** M.A. Eleffendi, University of Nottingham 16:40 T_J-IGBT-Driver: Junction Temperature
- 16:40 TJ-IGBT-Driver: Junction Temperature Measurement during Operation M. Denk, University of Bayreuth
- 17:10 Discussion
- 17:30 End of 1st workshop day
- 19:30 Dinner at XII Apostel / Hannover

Programme

Inursday, 22 October 2015		
9:00	Start of 2nd Day	
Introduction		
9:00	Gate Driver for WBG - Challenges of the Future S. Araujo, University of Kassel	
Session -	MOSFET and Wide Band Gap	
	High Side Driving under High-Switching Speeds S. Araujo, University of Kassel	
10:00	Discussion	
10:15	Coffee break	
10:45	WBG Drive Value Proposition F. Gringore, Rohm Semiconductor	
11:05	Advanced Gate Driver for IGBT and SiC MOSFet M. Lauria , STMicroelectronics	
Session - Robustness		
11:35	High Temperature Semiconductor Solutions for Gate Driver Applications P. Delatte, CISSOID	
12:05	250°C High Temperature Gate Driver for GaN Power Devices N. Kordas, Fraunhofer IMS	
12:35	Discussion	
12:45	Lunch	
Session -	Advanced & Euture Concents	
14:00	"Smart Converter" Technology and Intelligent Gate Drives: Challenges & Benefits A. Bryant, Amantys / Maschinenfabrik Reinhausen	
14:30	Automotive IGBT-Driver for Ignition Applications J. Pianka, Fairchild Semiconductor	
15:00	Case Study: Driver for WBG M. Hornkamp, Power Integrations	
15:20	Final Discussion	
16:00	End of Workshop	
16:00	Optional: Lab Tour Institute for Drive Systems and Power Electronics - Leibniz Universität Hannover A. Mertens, Leibniz Universität Hannover	